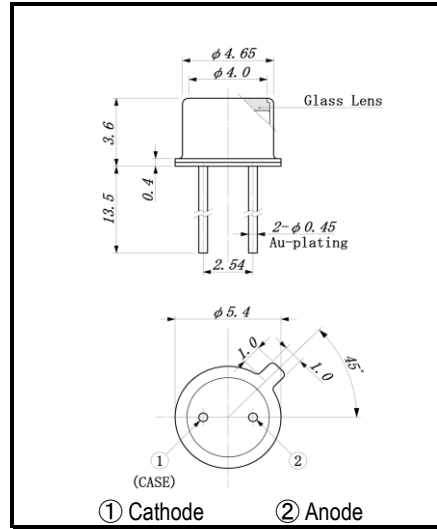
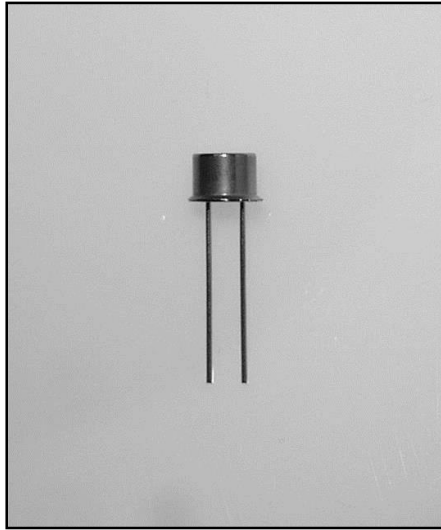


LS1060TM

Infrared Emitting Diode



① Cathode ② Anode
Dimensions (Unit:mm)

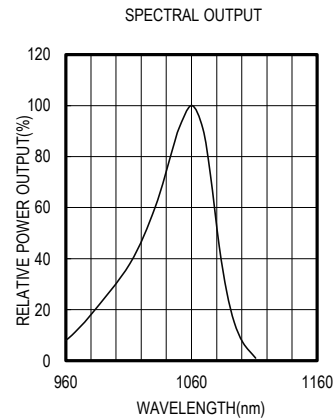
- FEATURES**
- High Reliability
 - High-output Power
- APPLICATIONS**
- Optical Switches
 - Optical Sensors

1. ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

ITEM	SYMBOL	RATINGS	UNIT
Forward Current (DC)	IF	100	mA
Forward Current (Pulse)*1	IFP	1	A
Reverse Voltage	VR	5	V
Power Dissipation	PD	180	mW
Operating Temp.	Topr	-20 TO 85	°C
Storage Temp.	Tstg	-30 TO 100	°C
Junction Temp.	Tj	100	°C
Lead Soldering Temp.*2	Tls	260	°C

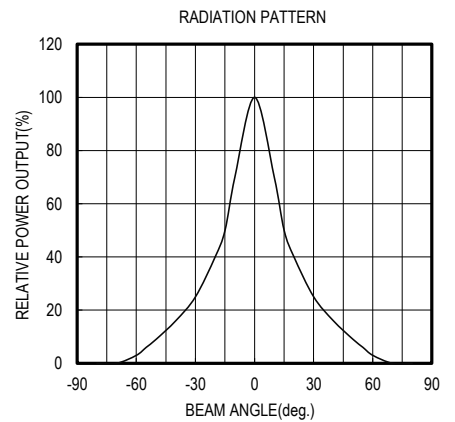
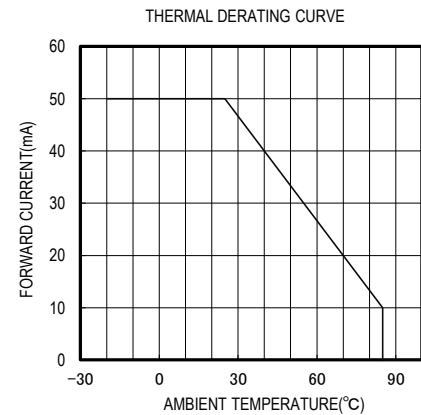
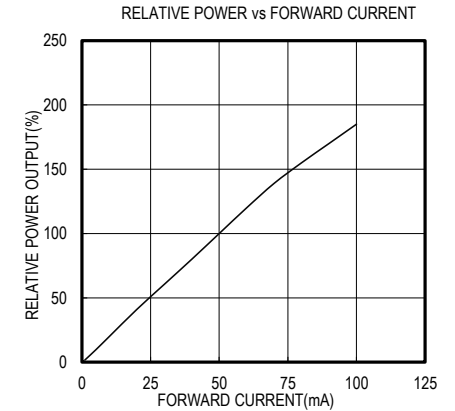
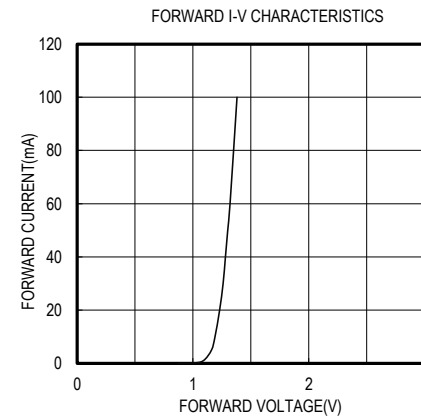
*1:Tw=10uS,T=1mS

*2:Time 5 Sec max,Position:Up to 3mm from the body



2. ELECTRICAL & OPTICAL CHARACTERISTICS (Ta=25°C)

ITEM	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Power Output	PO	IF=50mA		15.0		mW
Forward Voltage	VF	IF=50mA		1.30	1.80	V
Reverse Current	IR	VR=5V			100	μ A
Peak Wavelength	λ_p	IF=50mA		1060		nm
Spectral Line Half Width	$\Delta \lambda$	IF=50mA		50		nm
Half Intensity Beam Angle	θ	IF=50mA		± 15		deg.



OPTRANS

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